

“HALF-BRIDGE” IGBT

V_{CES} = 1200V
I_c = 150A
V_{CE(ON)} typ. = 1.7V
@I_c = 150A

Feature

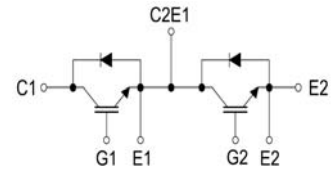
- IGBT New Technology
- Low V_{CE} (sat)
- Low Turn-off losses
- Short tail current
- Positive temperature coefficient

Application

- AC & DC Motor controls
- General purpose inverters
- Optimized for high current inverter (AC TIG Welding machines)
- Servo Controls
- UPS, Robotics



Package : V3



Absolute Maximum Ratings @ T_j = 25°C (Per Leg)

Symbol	Parameter	Condition	Ratings	Unit
V _{CES}	Collector-to-Emitter Voltage	V _{GE} = 0V, I _c = 6mA	1200	V
I _c	Continuous Collector Current		150	A
I _{c(puls)}	Pulsed collector current, t _p limited by T _{jmax}		450	A
V _{GE}	Gate emitter voltage		± 20	V
V _{iso}	Isolation Voltage test	AC @ 1 minute	2500	V
T _j	Junction Temperature		-40 ~ 150	°C
T _{stg}	Storage Temperature		-40 ~ 125	°C
Weight	Weight of Module		360	g
Md	Mounting torque with screw M5		2.0	N.m
	Terminal connection torque		2.0	N.m

Static Characteristics @ T_j = 25°C (unless otherwise specified)

Parameters		Min	Typ	Max	Unit	Test conditions
V _{(BR)CES}	Collector-to-Emitter Breakdown Voltage	1200	—	—	V	V _{GE} = 0V, I _c = 6mA
V _{CE(ON)}	Collector-to-Emitter Saturation Voltage	1.4	1.7	2.1		I _c = 150A, V _{GE} = 15V
V _{GE(th)}	Gate Threshold Voltage	5.0	5.8	6.5		V _{CE} = V _{GE} , I _c = 6mA
I _{CES}	Zero Gate Voltage Collector Current	—	—	20	μA	V _{GE} = 0V, V _{CE} = 1200V
I _{GES}	Gate-to-Emitter Leakage Current	—	—	600	nA	V _{CE} = 0V, V _{GE} = 20V
R _{GINT}	Integrated gate resistor	—	5	—	Ω	

